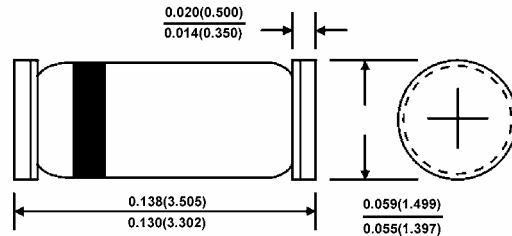




# BAS85

## 200mW Hermetically Sealed Glass Fast Switching Schottky Barrier Diodes

### MINI MELF



Dimensions in inches and (millimeters)

### Features

- ✧ Low forward voltage drop
- ✧ LL-34( Mini-MELF) package
- ✧ Through-Hole device type mounting
- ✧ Hermetically sealed glass
- ✧ Compression bonded construction
- ✧ All external surfaces are corrosion resistant and terminals are readily solderable
- ✧ RoHS compliant
- ✧ Solder Hot Dip Tin (Sn) lead finish

### Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

#### Maximum Ratings

Type Number	Symbol	Value	Units
Power Dissipation	P <sub>d</sub>	200	mW
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	30	V
Maximum DC Blocking Voltage	V <sub>R</sub>	30	V
Average Forward Rectified Current	I <sub>F(AV)</sub>	200	mA
Peak Forward Surge Current	I <sub>FSM</sub>	4	A
Operating Junction Temperature	T <sub>J</sub>	125	°C
Storage Temperature Range	T <sub>STG</sub>	-65 to + 125	°C

#### Electrical Characteristics

Type Number	Symbol	Min	Typ	Max	Units
Breakdown Voltage I <sub>R</sub> =10uA	B <sub>V</sub>	30			V
Reverse Leakage Current V <sub>R</sub> =25V	I <sub>R</sub>			2	uA
Forward Voltage I <sub>F</sub> =0.1mA I <sub>F</sub> =1.0mA I <sub>F</sub> = 10mA I <sub>F</sub> =30mA I <sub>F</sub> =100mA	V <sub>F</sub>			0.24 0.32 0.40 0.50 0.80	V
Reverse Recovery Time (Note 1)	T <sub>rr</sub>		5		nS
Junction Capacitance V <sub>R</sub> =1V, f=1.0MHz	C <sub>j</sub>			10	pF

Notes: 1. Reverse Recovery Test Conditions: I<sub>F</sub>= I<sub>R</sub> =10mA, R<sub>L</sub>=100Ω, I<sub>RR</sub>=1mA